



10MQ030N SCHOTTKY RECTIFIER

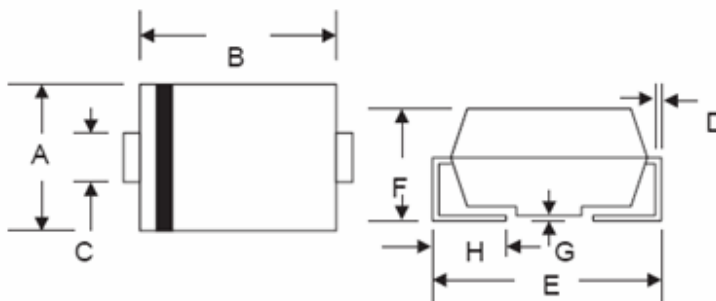
Applications:

- Disk Drives
- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Battery Charging

Features:

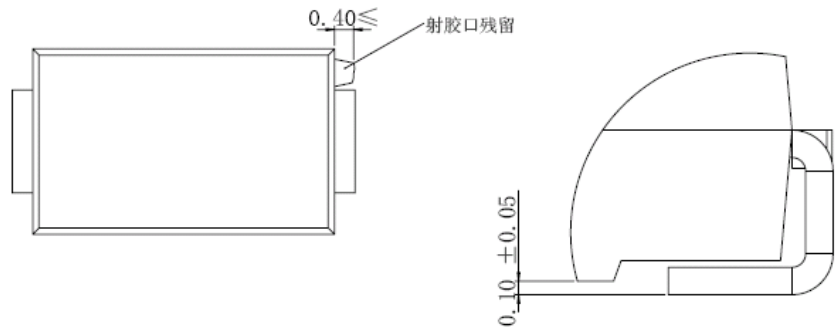
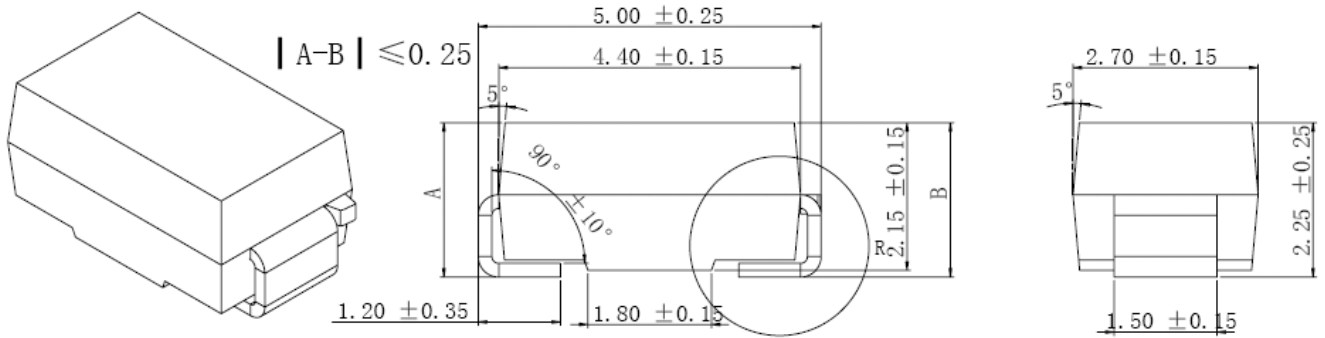
- Small foot print, surface moutable
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Mechanical Dimensions (In mm / Inches):



SMA/DO-214AC				
Dim	Min	Max	Min	Max
A	2.50	2.90	0.098	0.114
B	4.00	4.60	0.157	0.181
C	1.40	1.60	0.055	0.063
D	0.152	0.305	0.006	0.012
E	4.80	5.28	0.189	0.208
F	2.00	2.44	0.079	0.096
G	0.051	0.203	0.002	0.008
H	0.76	1.52	0.030	0.060
	In mm		In inch	

OPTION 1



OPTION2 (JK)

SMA



Marking Diagram:



Where XXXXX is YYWWL

- S = Device Type
- A = Package Type
- 1 = Forward Current (1A)
- E = Reverse Voltage (30V)
- YY = Year
- WW = Week
- L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
10MQ030N	SMA (Pb-Free)	5000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	30	V
Max. Average Forward Current	$I_{F(AV)}$	50% duty cycle @ $T_L=105^{\circ}C$, rectangular wave form On PC board 9mm ² island	1.0	A
Max. Peak One Cycle Non-Repetitive Surge Current (per leg)	I_{FSM}	8.3 ms, half Sine pulse	25	A



Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop*	V_{F1}	@ 1 A, Pulse, $T_J = 25\text{ }^\circ\text{C}$	0.45	V
	V_{F2}	@ 1 A, Pulse, $T_J = 100\text{ }^\circ\text{C}$	0.35	V
Max. Reverse Current *	I_{R1}	@ $V_R = \text{Rated } V_R$, Pulse, $T_J = 25\text{ }^\circ\text{C}$	1	mA
	I_{R2}	@ $V_R = \text{Rated } V_R$, Pulse, $T_J = 100\text{ }^\circ\text{C}$	25	mA
Max. Junction Capacitance	C_T	@ $V_R = 5\text{V}$, $T_C = 25\text{ }^\circ\text{C}$ $f_{SIG} = 1\text{MHz}$	38	PF
Typical Series Inductance	L_S	Measured lead to lead 5 mm from package body	2.0	nH
Max. Voltage Rate of Change	dv/dt	-	10,000	V/ μs

* Pulse Width < 300 μs , Duty Cycle < 2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Max. Junction Temperature	T_J	-	-55 to +125	$^\circ\text{C}$
Max. Storage Temperature	T_{stg}	-	-55 to +150	$^\circ\text{C}$
Maximum Thermal Resistance Junction to Case	$R_{\theta JA}$	DC operation	86	$^\circ\text{C/W}$
Approximate Weight	wt	-	0.11	g
Case Style	SMA			

Figure 1
Typical Forward Characteristics

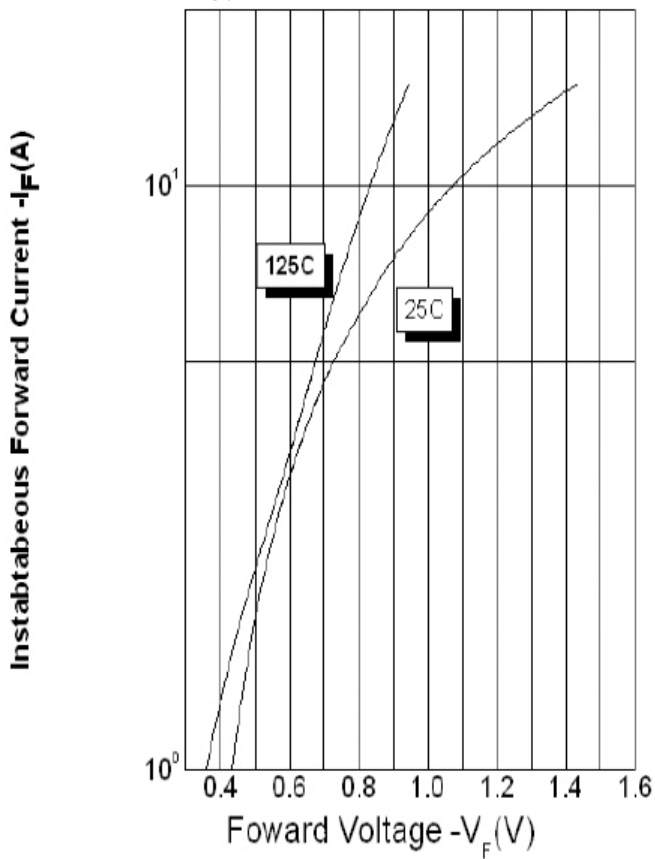


Figure 2
Typical Reverse Characteristics

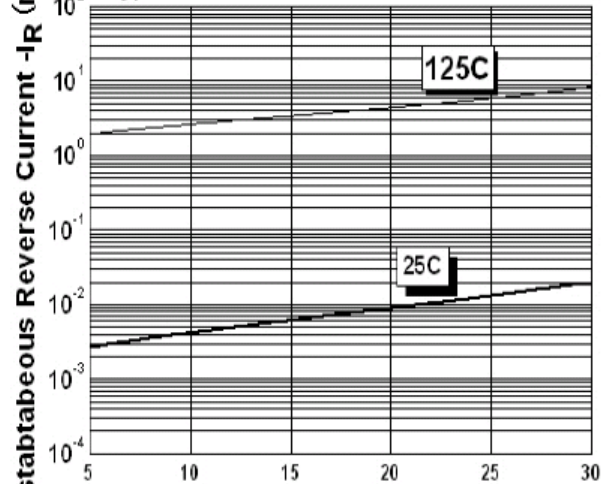
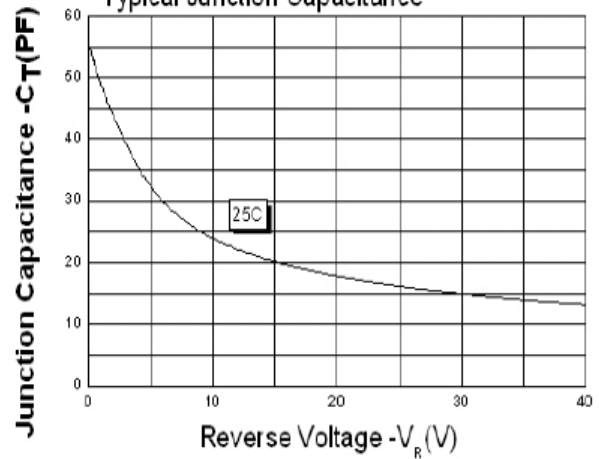


Figure 3 Reverse Voltage $-V_R$ (V)
Typical Junction Capacitance





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